## Single Channel 10A High Speed Low-Side MOSFET Driver

The NCP81074 is a single channel, low-side MOSFET driver. It is capable of providing large peak currents into capacitive loads. This driver can deliver a 7 A peak current at the Miller plateau region to help reduce the Miller effect during MOSFETs switching transitions. It exhibits a split output configuration allowing the user to control the turn on and turn off slew rates. This part is available in SOIC-8 and DFN8 2x2 mm packages.

## Features

- High Current Drive Capability $\pm 10 \mathrm{~A}$
- TTL/CMOS Compatible Inputs Independent of Supply Voltage
- High Reverse Current Capability (10 A) Peak
- 4 ns Typical Rise and 4 ns Typical Fall Times with 1.8 nF Load
- Fast Propagation Delay Times of 15 ns with Input Falling and 15 ns with Input Rising
- Input Voltage Range from 4.5 V to 20 V
- Split Output Configuration
- Dual Input Design Offering Drive Flexibility
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant


## Applications

- Server Power
- Telecommunication, Datacenter Power
- Synchronous Rectifier
- Switch Mode Power Supply
- DC/DC Converter
- Power Factor Correction
- Motor Drive
- Renewable Energy, Solar Inverter

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## ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 2 of this data sheet.

ORDERING INFORMATION

| Device | Temperature <br> Range ( ${ }^{\circ}$ C) | Marking | Input Type | Package Type | Shipping $^{\dagger}$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| NCP81074AMNTBG | -40 to +140 | CL | Fixed Digital Threshold | DFN8 2x2 <br> (Pb-Free) | $3000 /$ Tape \& Reel |
| NCP81074BMNTBG | -40 to +140 | CM | VDD Based Threshold | DFN8 2x2 <br> (Pb-Free) | $3000 /$ Tape \& Reel |
| NCP81074ADR2G | -40 to +140 | NCP81074A | Fixed Digital Threshold | SOIC-8 <br> (Pb-Free) | $2500 /$ Tape \& Reel |
| NCP81074BDR2G | -40 to +140 | NCP81074B | VDD Based Threshold | SOIC-8 <br> (Pb-Free) | $2500 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## BLOCK DIAGRAM



Figure 1. NCP81074 Block Diagram

## NCP81074A, NCP81074B

PIN DESCRIPTION

| Pin No. | Symbol | Description |
| :---: | :---: | :--- |
| 1 | IN+ | Non-Inverting Input which has logic compatible threshold and hysteresis. If not used, this pin should be <br> connected to either VDD or GND. It should not be left unconnected. |
| 2 | GND | Common ground. This ground should be connected very closely to the source of the power MOSFET. |
| 3 | GND | Common ground. This ground should be connected very closely to the source of the power MOSFET. |
| 4 | OUTL | Sink pin. Connect to Gate of MOSFET. |
| 5 | OUTH | Source Pin. Connect to Gate of MOSFET. |
| 6 | VDD | Power Supply Input Pin. |
| 7 | VDD | Power supply Input Pin. |
| 8 | IN- | Inverting Input which has logic compatible threshold and hysteresis. If not used, this pin should be connect- <br> ed to either VDD or GND. It should not be left unconnected |



Figure 2. TYPICAL APPLICATION CIRCUIT

ABSOLUTE MAXIMUM RATINGS

| Parameter |  | Value |  | Unit |
| :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Max |  |
| Supply Voltage | VDD | -0.3 | 24 | V |
| Output Current (DC) | lout_dc | 0.6 |  | A |
| Reverse Current (Pulse<1 $\mu \mathrm{s}$ ) |  |  | 10 | A |
| Output Current (Pulse<0.5 $\mu \mathrm{s}$ ) | lout_pulse | 10 |  | A |
| Input Voltage | IN+, $\mathrm{IN}-$ | -6 | 24 | V |
| Output Voltages | OUTH, OUTL | -0.3 | VDD + 0.3 | V |
| Output Voltages (Pulse<0.5 $\mu \mathrm{s}$ ) | OUTH, OUTL | -3.0 | VDD + 3.0 | V |
| Junction Operation Temperature | $\mathrm{T}_{\mathrm{J}}$ | -40 | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature | $\mathrm{T}_{\text {stg }}$ | -65 | 160 |  |
| Electrostatic Discharge | Human body model, HBM | 4000 |  | V |
|  | Charge device model, CDM | 1000 |  |  |
| OUT Latch-up Protection |  | 500 |  | mA |
| Moisture Sensitivity Level (MSL) |  | MSL1 |  |  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

| Parameter | Rating | Unit |
| :--- | :---: | :---: |
| VDD supply Voltage | 4.5 to 20 | V |
| IN+, IN- input voltages | -5 to 20 | V |
| Junction Temperature Range | -40 to +140 | ${ }^{\circ} \mathrm{C}$ |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 1. THERMAL INFORMATION

| Package | Theta JA $\left({ }^{\circ} \mathbf{C} / \mathbf{W}\right)$ | Theta JC $\left({ }^{\circ} \mathbf{C} / \mathbf{W}\right)$ |
| :---: | :---: | :---: |
| DFN-8 $2 \times 2$ | 80.3 | 11.9 |
| SOIC-8 | 115 | 50 |

Table 2. ELECTRICAL CHARACTERISTICS (Note 1) (Typical values: $\mathrm{VDD}=12 \mathrm{~V}$, 1 uF from VDD to GND,TA $=\mathrm{TJ}=$ $-40^{\circ} \mathrm{C}$ to $140^{\circ} \mathrm{C}$, typical at $\mathrm{T}_{\mathrm{AMB}}=25^{\circ} \mathrm{C}$, unless otherwise specified)

$|$| Parameter | SYMBOL | Test Conditions | MIN | TYP | MAX | Unit |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: | :---: |


| VUPPLY VOLTAGE | VDD Under Voltage Lockout (rising) | $\mathrm{V}_{\text {CCR }}$ | VDD rising | 3.7 | 3.9 | 4.1 |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| VDD Under Voltage Lockout (Falling) | $\mathrm{V}_{\text {CCF }}$ | VDD falling | 3.4 | 3.6 | 3.8 | V |
| VDD Under Voltage Lockout (hysteresis) | $\mathrm{V}_{\text {CCH }}$ |  |  | 300 |  | mV |
| Operating Current (no switching) | $\mathrm{I}_{\mathrm{DD}}$ |  |  | 1.2 | 2 | mA |
| VDD Under Voltage Lockout to Output <br> Delay (Note 1) |  |  |  | 10 |  | $\mu \mathrm{~s}$ | INPUTS


| NCP81074A High Threshold | $\mathrm{V}_{\text {thH }}$ | Input rising from logic low | 1.9 | 2.1 | 2.3 | V |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| NCP81074A Low Threshold | $\mathrm{V}_{\text {thL }}$ | Input falling from logic high | 1.1 | 1.3 | 1.5 | V |
| VIN_HYS | Input Signal Hysteresis |  |  | 0.8 |  | V |
| NCP81074B High Threshold | $\mathrm{V}_{\text {thH }}$ | Input rising from logic low (VDD $=8 \mathrm{~V}$ to 12 V ) | $\begin{aligned} & \hline \text { VDD } \\ & -3.5 \end{aligned}$ | $\begin{aligned} & \hline \text { VDD } \\ & -3.1 \end{aligned}$ | $\begin{aligned} & \hline \text { VDD } \\ & -2.7 \end{aligned}$ | V |
| NCP81074B Low Threshold | $\mathrm{V}_{\text {thL }}$ | Input falling from logic high (VDD $=8 \mathrm{~V}$ to 12 V ) | $\begin{aligned} & \text { GND } \\ & +2.6 \end{aligned}$ | $\begin{aligned} & \text { GND } \\ & +2.9 \end{aligned}$ | $\begin{gathered} \text { GND } \\ +3.2 \end{gathered}$ | V |
| IN- Pull-up Resistor | $\mathrm{R}_{\text {in- }}$ |  |  | 200 |  | k $\Omega$ |
| IN+ Pull-Down Resistor | $\mathrm{R}_{\text {in+ }}$ |  |  | 200 |  | k $\Omega$ |

OUTPUTS

| Output Resistance High | $\mathrm{R}_{\mathrm{OH}}$ | IOUT $=-10 \mathrm{~mA}$ | 0.4 | 0.8 | $\Omega$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Output Resistance Low | $\mathrm{R}_{\mathrm{OL}}$ | IOUT $=+10 \mathrm{~mA}$ | 0.4 | 0.8 | $\Omega$ |
| Peak Source Current ${ }^{(2)}$ | $I_{\text {Source }}$ | $\begin{aligned} & \text { OUT = GND } \\ & 200 \text { ns Pulse } \end{aligned}$ | 10 |  | A |
| Miller Plateau Source Current ${ }^{(2)}$ | $I_{\text {Source }}$ | $\begin{aligned} & \text { OUT = } 5.0 \mathrm{~V} \\ & 200 \mathrm{~ns} \text { Pulse } \end{aligned}$ | 7 |  | A |
| Peak Sink Current ${ }^{(2)}$ | $I_{\text {Sink }}$ | $\begin{aligned} & \text { OUT = VDD } \\ & 200 \text { ns Pulse } \end{aligned}$ | 10 |  | A |
| Miller Plateau Sink Current ${ }^{(2)}$ | $I_{\text {Sink }}$ | $\begin{aligned} & \text { OUT = 5.0 V } \\ & 200 \text { ns Pulse } \end{aligned}$ | 7 |  | A |

## NCP81074A, NCP81074B

Table 2. ELECTRICAL CHARACTERISTICS (Note 1) (Typical values: $\mathrm{VDD}=12 \mathrm{~V}$, 1 uF from VDD to $\mathrm{GND}, \mathrm{TA}=\mathrm{TJ}=$ $-40^{\circ} \mathrm{C}$ to $140^{\circ} \mathrm{C}$, typical at $\mathrm{T}_{\mathrm{AMB}}=25^{\circ} \mathrm{C}$, unless otherwise specified)

| Parameter | SYMBOL | Test Conditions | MIN | TYP | MAX | Unit |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: | :---: |


| Propagation Delay Time Low to High, IN <br> Rising (IN to OUT) (Note 2) | $\mathrm{t}_{\mathrm{d} 1}$ | C $_{\text {Load }}=1.8 \mathrm{nF}$ |  | 15 | 27 |
| :--- | :---: | :---: | :---: | :---: | :---: |
| Propagation Delay Time High to Low, IN <br> Falling (IN to OUT) (Note 2) | $\mathrm{t}_{\mathrm{d} 2}$ | C $_{\text {Load }}=1.8 \mathrm{nF}$ |  | 15 | 27 |
| Rise Time (Note 2) | $\mathrm{t}_{\mathrm{r}}$ | C $_{\text {Load }}=1.8 \mathrm{nF}$ | ns |  |  |
| Fall Time (Note 2) | $\mathrm{t}_{\mathrm{f}}$ | C $_{\text {Load }}=1.8 \mathrm{nF}$ | 4 | 7 | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. All Limits are $100 \%$ tested at TAMB $=25^{\circ} \mathrm{C}$ and guaranteed across temperature by design and statistical analysis.
2. Guaranteed by characterization. *See timing Waveforms.

Table 3. LOGIC TRUTH TABLE

|  | IN- |  |  | OUT <br> IN + |
| :---: | :---: | :---: | :---: | :---: |
| L | L | OUTH | OUTL | (OUTH \& OUTL CONNECTED <br> TOGETHER) |
| L | H | $\mathrm{HIGH}-Z$ | L | L |
| H | L | $\mathrm{H}-Z$ | L | H |
| H | H | $\mathrm{HIGH}-Z$ | $\mathrm{LIGH}-Z$ | L |



Figure 3. Non-inverting Input Driver Operation


Figure 4. Inverting Input Driver Operation

## NCP81074A, NCP81074B

TYPICAL CHARACTERISTICS


Figure 5. Supply Current vs. Switching Frequency, $\mathrm{V}_{\mathrm{DD}}=12 \mathrm{~V}$


Figure 7. Fall Time vs. Temperature $C_{\text {LOAD }}=1.8 \mathrm{nF}$


Figure 9. Propagation Delay $T_{D 1}$ vs. Supply Voltage


Figure 6. Supply Current vs. Switching Frequency, $\mathrm{V}_{\mathrm{DD}}=4.5 \mathrm{~V}$


Figure 8. Rise Time vs. Temperature $C_{\text {load }}=1.8 \mathrm{nF}$


Figure 10. Propagation Delay $\mathrm{T}_{\mathrm{D} 2}$ vs. Supply Voltage

## NCP81074A, NCP81074B

TYPICAL CHARACTERISTICS


Figure 11. Supply Current vs. Supply Voltage $C_{\text {LOAD }}=2.2 \mathrm{nF}$


Figure 13. Reverse Current, $\mathrm{P}_{\mathrm{MOS}(o n)}, \mathrm{P}_{\mathrm{MOS}(\mathrm{off})}$


Figure 12. Supply Current vs. Supply Voltage $C_{\text {LOAD }}=4.7 \mathrm{nF}$


Figure 14. Reverse Current, $\mathrm{P}_{\mathrm{MOS}(o f f)}, \mathrm{P}_{\mathrm{MOS}(o n)}$


Figure 15. Supply Current vs. Supply Voltage

BENCH WAVEFORMS - Non-Inverting Input


Figure 16. Rise Time with 1.8 nF Load


Figure 18. Propagation Delays with 1.8 nF Load


Figure 17. Fall Time with 1.8 nF Load


Figure 19. Propagation Delays with 1.8 nF Load

NCP81074A, NCP81074B
BENCH WAVEFORMS - Inverting Input


Figure 20. Rise Time with 1.8 nF Load


Figure 22. Propagation Delays with 1.8 nF Load


Figure 21. Fall Time with 1.8 nF Load


Figure 23. Propagation Delays with 1.8 nF Load

## PCB LAYOUT RECOMMENDATION

Proper component placement is extremely important in high current, fast switching applications to provide appropriate device operation and design robustness. The NCP81074 gate driver exhibits a powerful output stage enabling large peak currents with fast rise and fall times. Eventhough the NCP81074 provides a split output configuration for slew rate control, a proper PCB layout is crucial to ensure maximum performance. The following circuit layout guidelines are strongly recommended when designing with the NCP81074.

- Place the driver close to the power MOSFET in order to have a low impedance path between the output pins and the gate. Keep the traces short and wide to minimize the parasitic inductance and accommodate for high peak currents.
- Place the decoupling capacitor close to the gate drive IC. Placing the VDD capacitor close to the pin and ground improves noise filtering. This capacitor supplies
high peak currents during the turn-on transition of the MOSFET. Using a low ESL chip capacitor is highly recommended.
- Keep a tight turn-on turn-off current loop paths to minimize parastic inductance. High di/dt will induce voltage spikes on the output pin and the MOSFET gate. Parallel the source and return signals taking advantage of flux cancellation.
- Since the NCP81074 is a $2 \times 2 \mathrm{~mm}$ package driving high peak currents into capacitive loads, adding a shielding ground plane helps in power dissipation and noise blocking. The ground plane should not be a current carrying path to any of the current loops.
- Any unused pin, should be pulled to either rail depending on the functionality of the pin to avoid any malfunction on the output. Please refer to the pin description table for more information.


Figure 24.

DFN8 2x2, 0.5P
CASE 506AA-01
ISSUE E
DATE 22 JAN 2010

## SCALE 4:1



NOTES:
. Dimensioning and tolerancing per ASME Y14.5M, 1994
CONTROLLING DIMENSION: MILLIMETERS.
2. CIMENSION B APPLIES TO PLATED

TERMINAL AND IS MEASURED BETWEEN
0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

|  | MILLIMETERS |  |
| :---: | :---: | :---: |
| DIM | MIN | MAX |
| A | 0.80 | 1.00 |
| A1 | 0.00 | 0.05 |
| A3 | 0.20 REF |  |
| b | 0.20 | 10.30 |
| D | 2.00 BSC |  |
| D2 | 1.10 | 1.30 |
| E | 2.00 BS |  |
| E2 | 0.70 | 0.90 |
| e | 0.50 BSC |  |
| K | 0.30 REF |  |
| L | 0.25 | 0.35 |
| L1 | ---1 | 0.10 |

## GENERIC <br> MARKING DIAGRAM*

DETAIL B optional construction

BOTTOM VIEW



XX = Specific Device Code
M = Date Code

- = Pb-Free Device
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{\nabla "}$, may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | DFN8, 2.0X2.0, 0.5MM PITCH | PAGE 1 OF 1 |

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SOIC-8 NB
CASE 751-07
ISSUE AK
SCALE 1:1
DATE 16 FEB 2011


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW
7. 751-01 THRU 751-06 AR
STANDARD IS 751-07.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC |  | 0.050 BSC |  |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0 | $0^{\circ}$ | $8^{\circ}$ | 0 |
|  | $\circ$ | 8 |  |  |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

## GENERIC

MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
= Year
$\begin{array}{ll}\mathrm{W} & =\text { Work Week } \\ \text { - } & =\text { Pb-Free Package }\end{array}$
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{=}$ ", may or may not be present. Some products may not follow the Generic Marking.
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## STYLES ON PAGE 2

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| DESCRIPTION: | SOIC-8 NB | PAGE 1 OF 2 |

[^0] rights of others.

SOIC-8 NB
CASE 751-07
ISSUE AK
DATE 16 FEB 2011

STYLE

| PIN 1. | EMITTER |
| ---: | :--- |
| 2. | COLLECTOR |
| 3. | COLLECTOR |
| 4. | EMITTER |
| 5. | EMITTER |
| 6. | BASE |
| 7. | BASE |
| 8. | EMITTER |
| STYLE 5: |  |
| PIN 1. | DRAIN |
| 2. | DRAIN |
| 3. | DRAIN |
| 4. | DRAIN |
| 5. | GATE |
| 6. | GATE |
| 7. | SOURCE |
| 8. | SOURCE |

STYLE 9:
PIN 1. EMITTER, COMMON
COLLECTOR, DIE \#1 COLLECTOR, DIE \#2 EMITTER, COMMON EMITTER, COMMON BASE, DIE \#2
BASE, DIE \#1
8. EMITTER, COMMON

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE

GATE
DRAIN
DRAIN
DRAIN
8. DRAIN

STYLE 17:
PIN 1. VCC
V2OUT
V10UT
V10UT
TXE
RXE
VEE
7. GND
8. ACC

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3

CATHODE 4
CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 25:
PIN 1. VIN
2. $\mathrm{N} / \mathrm{C}$

REXT
GND
IOUT
IOUT
IOUT
8. IOUT

## STYLE 29

PIN 1. BASE, DIE \#
EMITTER, \#1
BASE, \#2
. EMITTER, \#2
5. COLLECTOR, \#2
6. COLLECTOR, \#2
7. COLLECTOR, \#1
8. COLLECTOR, \#1

STYLE
PIN 1. COLIECTOR,
2. COLLECTOR, \#
3. COLLECTOR, \#2

COLLECTOR, \#2
BASE, \#2
. EMITTER, \#2
7. BASE, \#1
8. EMITTER, \#1

STYLE 6:
PIN 1. SOURCE
DRAIN
3. DRAIN
4. SOURCE

SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT

GROUND
GROUND
BIAS 2
7. INPUT
8. GROUND

STYLE 14
PIN 1. N-SOURCE
2. N-GATE
. P-SOURCE
P-GATE
5.DRAIN
6. P-DRAIN
7. N-DRAIN
8. N -DRAIN

STYLE 18
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 22 :
PIN 1. I/O LINE
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 26:
PIN 1. GND
2. $\mathrm{dv} / \mathrm{dt}$
3. ENABLE
4. ILIMIT

SOURCE
SOURCE
SOURCE
8. VCC

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
. SOURCE 1/DRAIN 2
SOURCE 1/DRAIN 2
8. GATE 1

STYLE 3
STYLE
2. DRAIN, DIE
2. DRAIN, \#1
2. DRAIN, \#
3. DRAIN, \#2
4. DRAIN, \#2
5. GATE, \#2
7. GATE, \#1
8. SOURCE, \#1

## STYLE 7

PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

## STYLE 11:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

## STYLE 15:

PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

## STYLE 19:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

## STYLE 23:

PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
8. COMMON CATHODE

## STYLE 8:

PIN 1. COLLECTOR, DIE \#1
2. BASE, \#1
3. BASE, \#2
4. COLLECTOR, \#2
5. COLLECTOR, \#2
6. EMITTER, \#2
7. EMITTER, \#1
8. COLLECTOR, \#1

## STYLE 12

PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

## STYLE 16:

PIN 1. EMITTER, DIE \#1
2. BASE, DIE \#1
3. EMITTER, DIE \#2
3. EMITTER, DIE
4. BASE, DIE \#2
4. BASE, DIE \#2
6. COLLECTOR, DIE \#2
7. COLLECTOR, DIE \#1
8. COLLECTOR, DIE \#1

## STYLE 20:

PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 24
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

## STYLE 28:

PIN 1. SW_TO_GND
2. DASIC $\bar{O} F F$
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

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| DESCRIPTION: | SOIC-8 NB | PAGE 2 OF 2 |

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